



DSS5240T

40V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

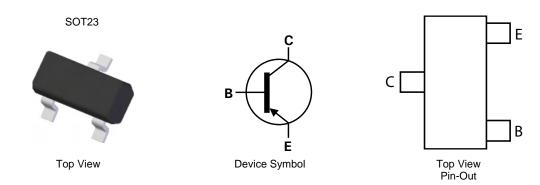
- BV_{CEO} > -40V
- I_C = -2A high Continuous Collector Current
- I_{CM} = -3A Peak Pulse Current
- Low Saturation Voltage -225mV Max @ I_C = -1A.
- R_{CE(sat)} = 90mΩ at 0.5A for a low equivalent on-resistance
- 730mW power dissipation
- Complimentary NPN Type: DSS4240T
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 63
- Weight 0.008 grams (approximate)

Application

- Gate Driving MOSFETs and IGBTs
- Load switch
- DC-DC converters
- Battery charging



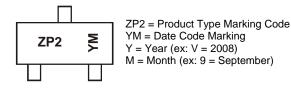
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS5240T-7	ZP2	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

Marking Information



Date Code Kev

Year	2008	2009	2010	2011	2012	2013	201	4 2	015	2016	2017	2018
Code	V	W	Χ	Υ	Z	A	В		С	D	E	F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Collector Current	I _{CM}	-3	А
Continuous Collector Current	lc	-2	А
Base Current	I_{B}	-300	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	730	mW
Power Dissipation (Note 6)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{ heta JA}$	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{\theta JA}$	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	$R_{ heta JL}$	75	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

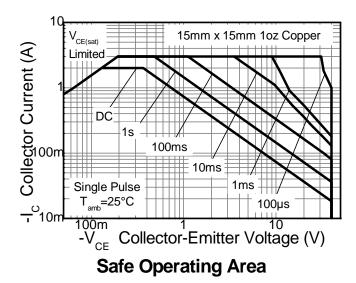
^{5.} For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

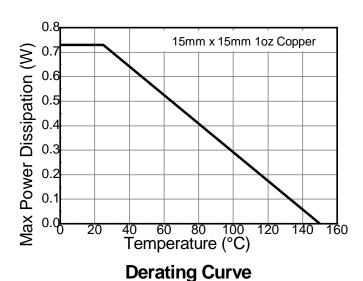
6. Same as note (5), except the device surface mounted on FR4 PCB with minimum recommended pad layout.

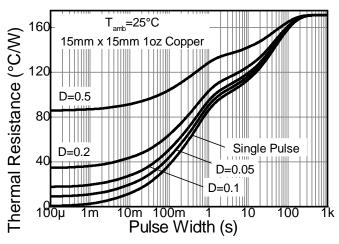
7. Thermal resistance from junction to solder-point (at the end of the collector lead).

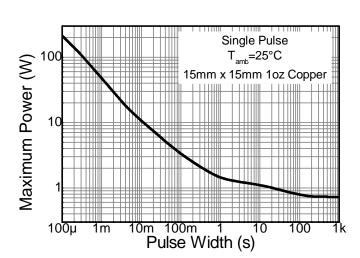


Thermal Characteristics and Derating information









Transient Thermal Impedance

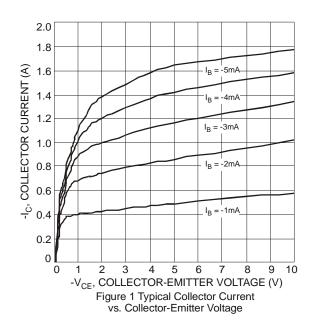
Pulse Power Dissipation

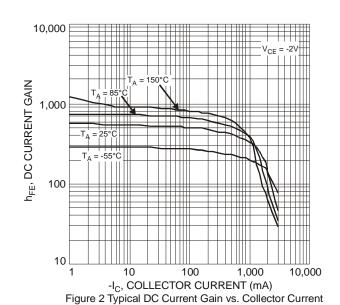


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage		-40	_	_	V	$I_C = -100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 8)	BV _{CEO}	-40	_	_	V	I _C = -10mA	
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	_		V	$I_E = -100\mu A$	
Collector-Base Cutoff Current	lana		_	-100	nA	$V_{CB} = -30V, I_{E} = 0$	
Collector-base Cutoff Current	I _{CBO}	_	_	-50	μΑ	$V_{CB} = -30V$, $I_E = 0$, $T_A = +150$ °C	
Emitter-Base Cutoff Current	I _{EBO}	_	_	-100	nA	$V_{EB} = -4V, I_{C} = 0$	
ON CHARACTERISTICS (Note 8)							
		300	_	_		$V_{CE} = -2V, I_{C} = -0.1A$	
DC Current Gain		260	_			$V_{CE} = -2V, I_{C} = -0.5A$	
DC Current Gain	h _{FE}	210	_	_		$V_{CE} = -2V$, $I_C = -1A$	
		100	_	_		$V_{CE} = -2V, I_{C} = -2A$	
	V _{CE(SAT)}	_	_	-100		$I_C = -100 \text{mA}, I_B = -1 \text{mA}$	
		_	45	-110		$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
Collector-Emitter Saturation Voltage		_	_	-225	mV	$I_C = -750 \text{mA}, I_B = -15 \text{mA}$	
		_	_	-225		$I_C = -1A$, $I_B = -50mA$	
		_	_	-350		$I_C = -2A$, $I_B = -200mA$	
Equivalent On-Resistance	R _{CE} (SAT)	_	90	220	mΩ	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$	
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	_	_	-1.1	V	$I_C = -2A$, $I_B = -200mA$	
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_	_	-0.75	V	$V_{CE} = -2V, I_{C} = -100mA$	
SMALL SIGNAL CHARACTERISTICS	SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	_	_	MHz	$V_{CE} = -10V, I_{C} = -100mA,$ f = 100MHz	
Output Capacitance	C _{ob}	_	_	28	pF	V _{CB} = -10V, f = 1MHz	

Notes: 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.







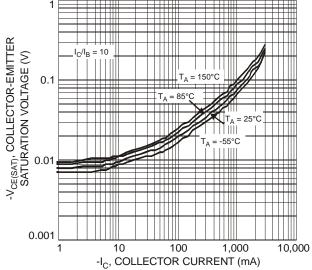


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

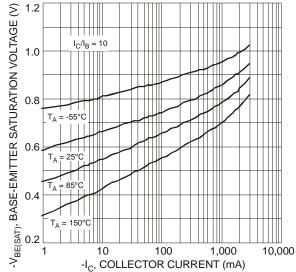


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

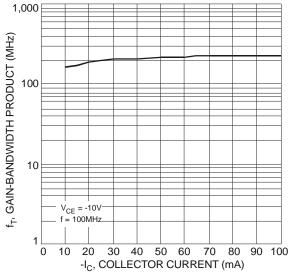


Figure 7 Typical Gain-Bandwidth Product vs. Collector Current

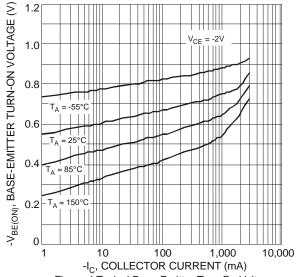


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

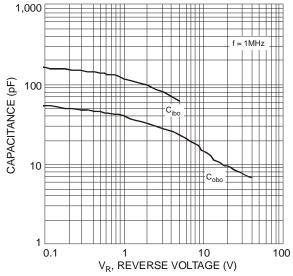
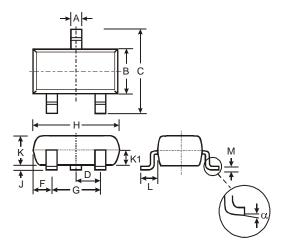


Figure 6 Typical Capacitance Characteristics



Package Outline Dimensions

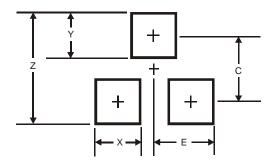
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
М	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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